

#### **Features**

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>

### **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

## **Applications**

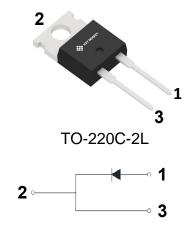
- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters





**Maximum Ratings** (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V		
$V_{RSM}$	Surge Peak Reverse Voltage	1300	V		
V <sub>R</sub>	DC Peak Reverse Voltage	1200	V		
I <sub>F</sub>	Continuous Forward Current	19 9.5 5	А	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =161°C	Fig. 3
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	26 18	А	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Half Sine Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Half Sine Pulse	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	46 36	А	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Half Sine Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Half Sine Pulse	Fig. 8
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Current	400 320	А	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Pulse	Fig. 8
P <sub>tot</sub>	Power Dissipation	100 43	w	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V <sub>R</sub> =0-650V	
∫i²dt	i²t value	10.6 6.5	A²s	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms	
T <sub>J</sub>	Operating Junction Range	-55 to +175	°C		
T <sub>stg</sub>	Storage Temperature Range	-55 to +135	°C		
	TO220-2L Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw	





### **Electrical Characteristics**

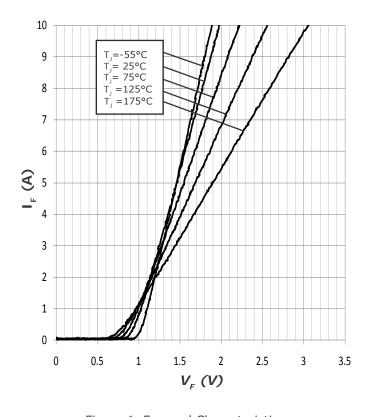
Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.4 1.9	1.8 3	V	I <sub>F</sub> = 5 A T <sub>J</sub> =25°C I <sub>F</sub> = 5 A T <sub>J</sub> =175°C	Fig. 1
I <sub>R</sub>	Reverse Current	20 40	150 300	μΑ	V <sub>R</sub> = 1200 V T <sub>J</sub> =25°C V <sub>R</sub> = 1200 V T <sub>J</sub> =175°C	Fig. 2
Q <sub>c</sub>	Total Capacitive Charge	27		nC	$V_R = 800 \text{ V, } I_F = 5A$ $di/dt = 200 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	390 27 20		pF	V <sub>R</sub> = 0 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 400 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 800 V, T <sub>J</sub> = 25°C, f = 1 MHz	Fig. 6
E <sub>c</sub>	Capacitance Stored Energy	8.0		μЈ	V <sub>R</sub> = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.5	°C/W	Fig. 9

## **Typical Performance**





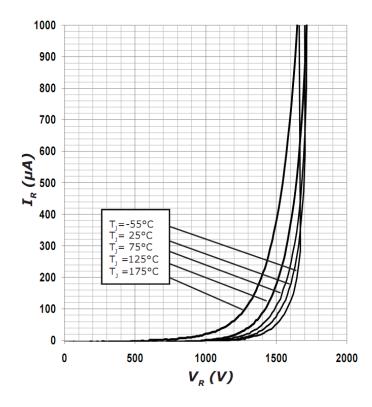
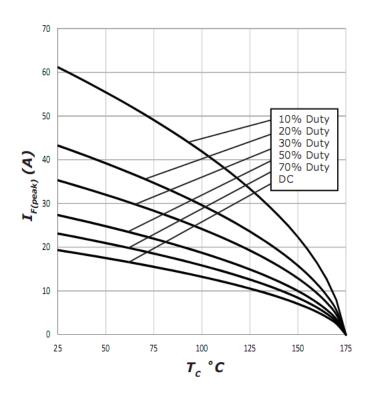


Figure 2. Reverse Characteristics



## **Typical Performance**



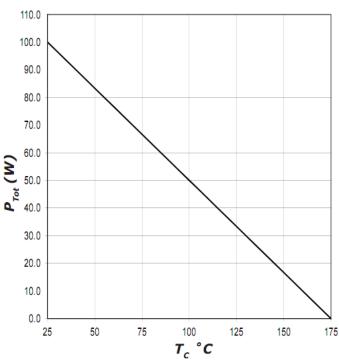


Figure 3. Current Derating

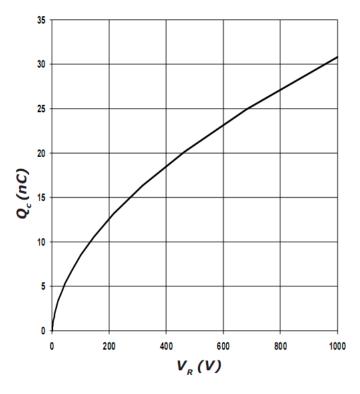


Figure 4. Power Derating

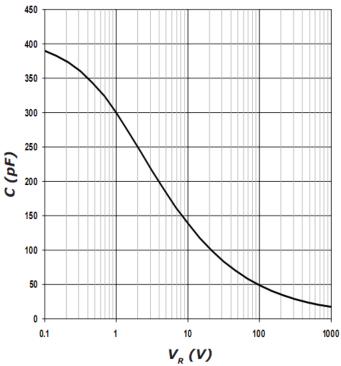


Figure 5. Recovery Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

### **Diode Model**

$$Vf_{T} = V_{T} + If * R_{T}$$

$$V_{T} = 0.96 + (T_{j} * -1.22*10^{-3})$$

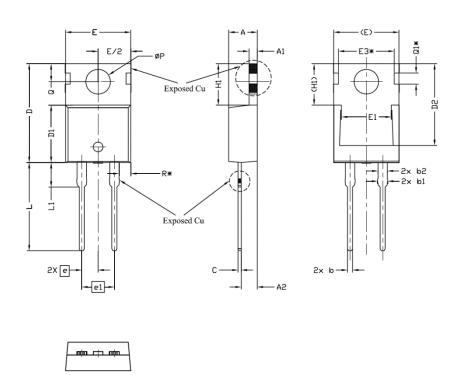
$$R_{T} = 0.08 + (T_{j} * 8.5*10^{-4})$$

$$V_{T} = R_{T}$$

Note: T<sub>i</sub> is diode junction temperature in degrees Celsius

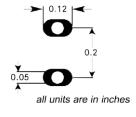


# Package Information TO-220C-2L



	[				
SYMBOL	MIN. NOM. MAX.			NOTES	
А	4,24	4.44	4,64		
A1	1.15	1.27	1.40		
A2	2.30	2.48	2.70		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20	1.45	1.70		
С	0.40	0.50	0.60		
D	14.70	15.37	16.00	4	
D1	8.82	8.92	9.02		
D2	12.43	12.73	12.83	5	
E	9.96	10.16	10.36	4,5	
E1	6,86	7.77	8,89	5	
E3*					
е					
e1					
H1	6.30	6.45	6.60	5,6	
L	13.47	13.72	13.97		
L1	3.60	3.80	4.00		
ØP	3.75	3.84	3,93		
Q	2,60 2,80		3,00		
Q1*					
R*					

## **Recommended Solder Pad Layout**



TO-220C-2L



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